

Dual N-Ch 30V MOSFETs

Features

- ★ Split Gate Trench MOS Technology
- ★ 100% EAS Guaranteed
- ★ Fast Switching Speed
- ★ Green Device Available

Applications

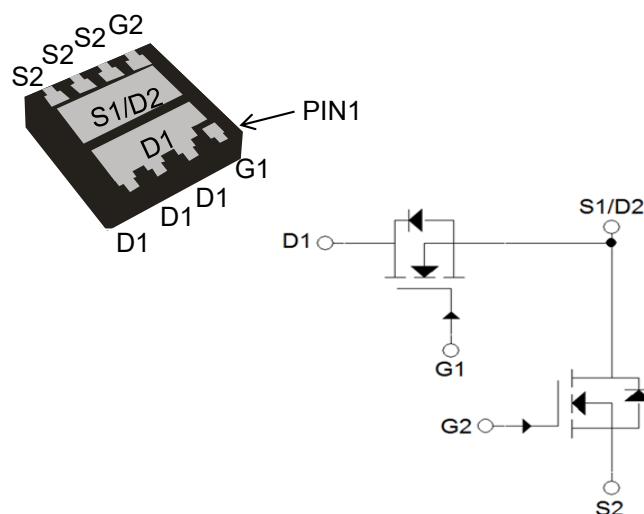
- ★ High Frequency Switching and Synchronous Rectification.
- ★ DC/DC Converter.

Product Summary



BVDSS	RDSON	ID
30V	5.5mΩ	45A

DFN5060-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	45	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	32	A
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	24	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	20	A
I_{DM}	Pulsed Drain Current ²	135	A
EAS	Single Pulse Avalanche Energy ³	29.8	mJ
I_{AS}	Avalanche Current	27	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	30	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	50	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4.6	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=20A$	---	5.5	7.2	$m\Omega$
		$V_{GS}=4.5V$, $I_D=15A$	---	8.5	11	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.2	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=20A$	---	67	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.7	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15V$, $V_{GS}=4.5V$, $I_D=15A$	---	8	---	nC
Q_{gs}	Gate-Source Charge		---	2.4	---	
Q_{gd}	Gate-Drain Charge		---	3.2	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=15A$	---	7.1	---	ns
T_r	Rise Time		---	40	---	
$T_{d(off)}$	Turn-Off Delay Time		---	15	---	
T_f	Fall Time		---	6	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	814	---	pF
C_{oss}	Output Capacitance		---	498	---	
C_{rss}	Reverse Transfer Capacitance		---	41	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V$, Force Current	---	---	45	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$I_F=20A$, $di/dt=100A/\mu s$,	---	15	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	25	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.1mH$, $I_{AS}=24A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Characteristics

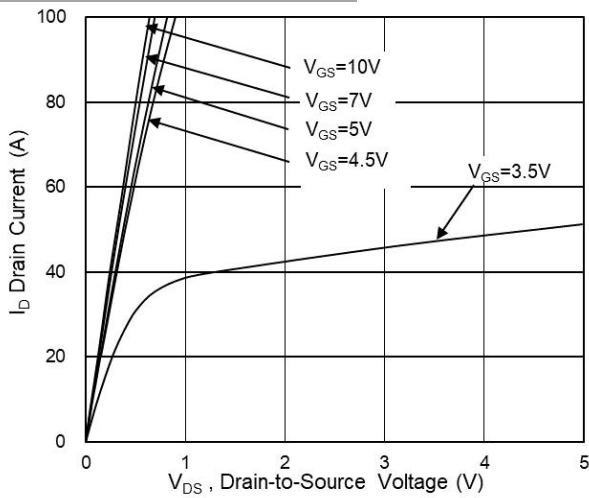


Fig.1 Typical Output Characteristics

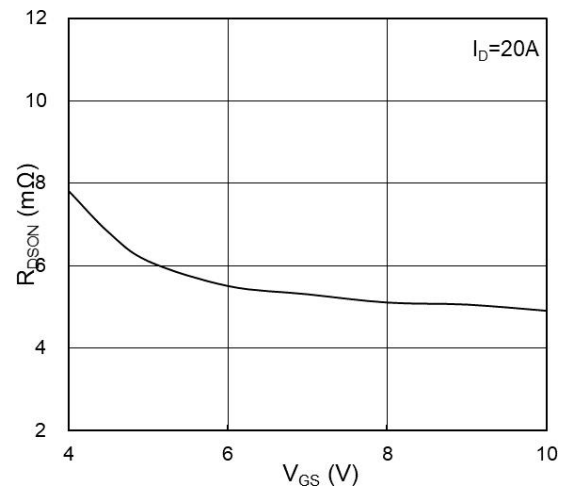


Fig.2 On-Resistance vs G-S Voltage

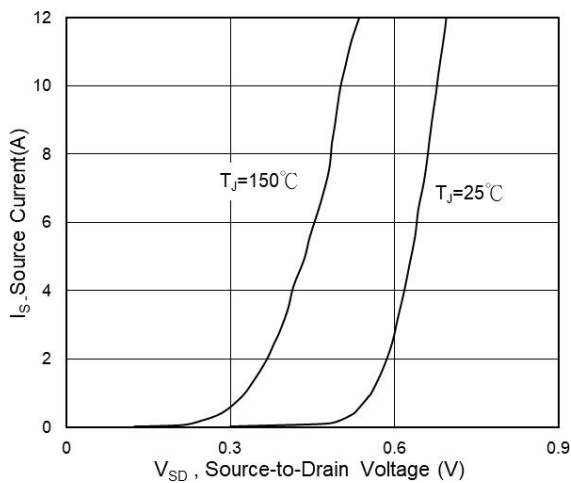


Fig.3 Source Drain Forward Characteristics

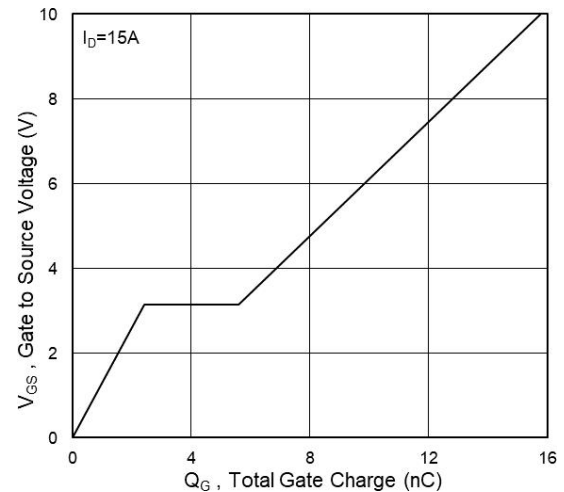


Fig.4 Gate-Charge Characteristics

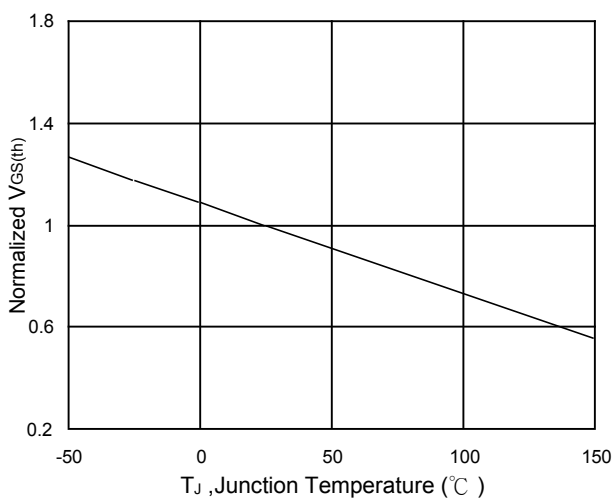


Fig.5 Normalized $V_{GS(th)}$ vs T_J

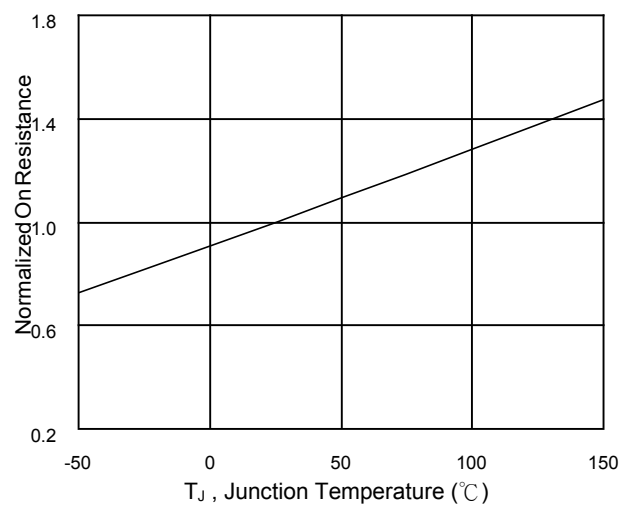


Fig.6 Normalized $R_{DS(on)}$ vs T_J

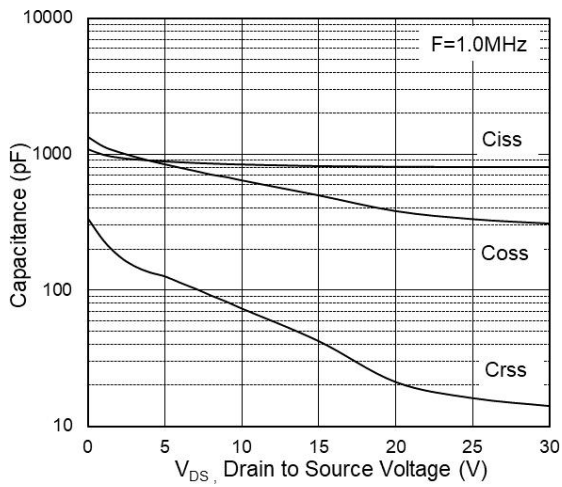


Fig.7 Capacitance

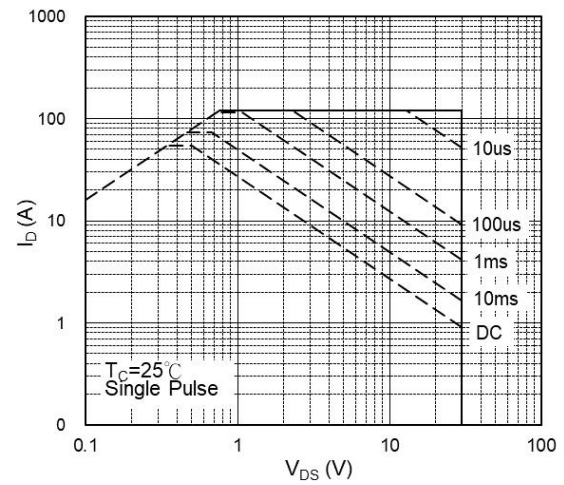


Fig.8 Safe Operating Area

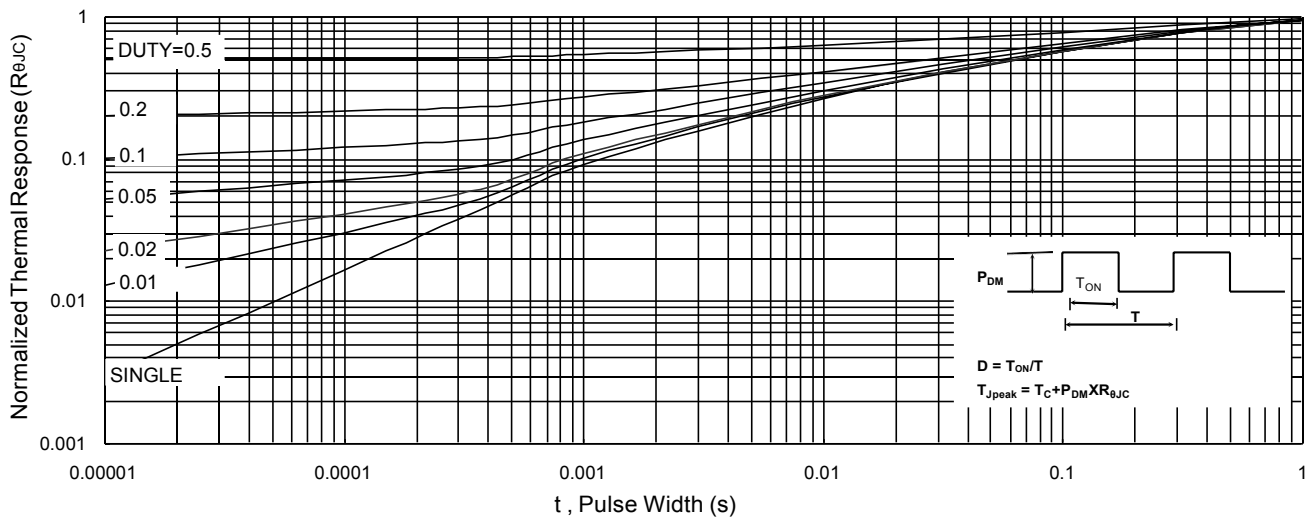


Fig.9 Normalized Maximum Transient Thermal Impedance

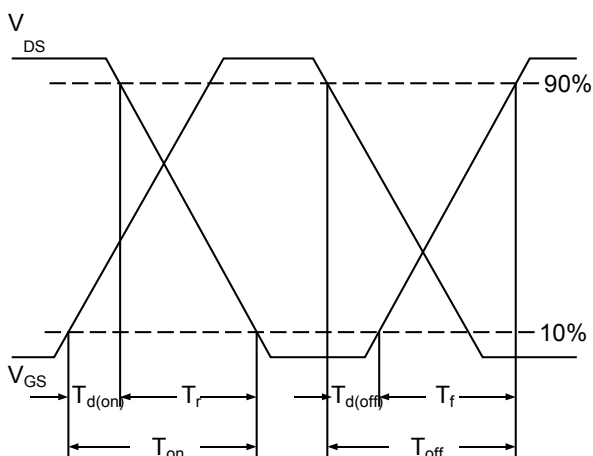


Fig.10 Switching Time Waveform

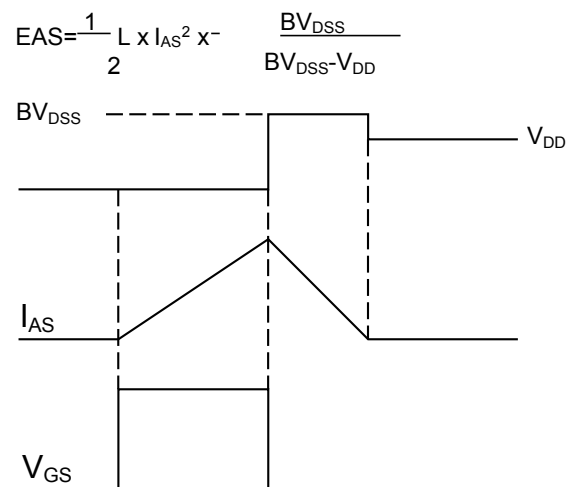
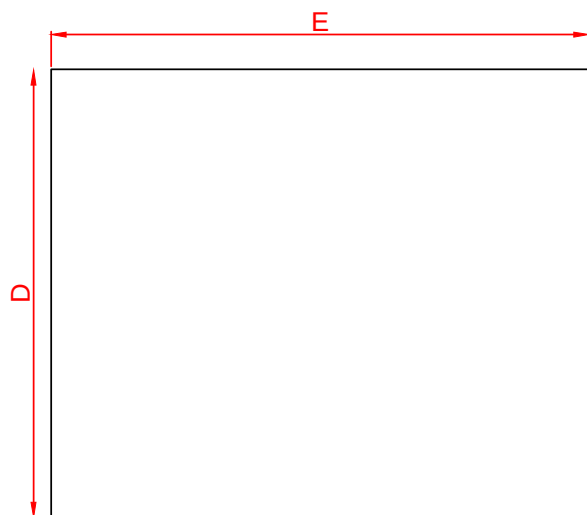
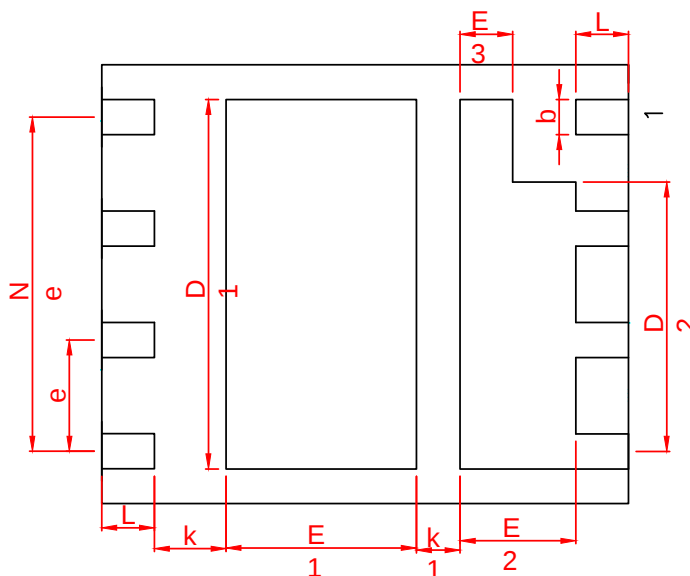


Fig.11 Unclamped Inductive Switching Waveform

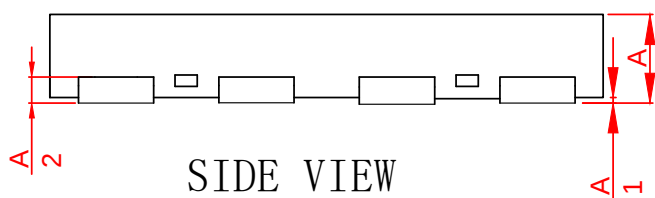
DFN5060-8L Package Information



TOP VIEW



BOTTOM VIEW



SIDE VIEW

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	0.70	0.75	0.80
* A1	0.00	0.02	0.05
* b	0.36	0.41	0.46
* A2	0.203 BSC		
* D	4.90	5.00	5.10
* D1	4.15	4.20	4.25
* D2	2.87	3.07	3.27
* E	5.90	6.00	6.10
* E1	2.02	2.17	2.32
E2	1.22	1.32	1.42
E3	0.55	0.60	0.65
* e	1.27 REF		
* Ne	BSC 3.81		
k	0.71	0.81	0.91
* k1	0.40	0.50	0.60
* L	0.55	0.60	0.65